

*ABSTRACT AMENDMENTS*

Replace the Abstract with:

A semiconductor device includes a semiconductor substrate 10, a channel layer 7, a Schottky layer ~~5a, 5b~~, a first layer 12 having a narrower band gap than the Schottky layer, a second layer 14 having band discontinuity with the Schottky layer, a gate electrode 4, an n+ layer 4, a source electrode 2, and a drain electrode 3. The first and second layers are inserted ~~in~~ within the Schottky layer, and the second layer is disposed on the first layer.